

# Driving atoms into materials using extreme photon fluxes



Workshop on Basic Research Needs  
for Materials under Extreme Conditions  
Bethesda, MD, 11 June 2007



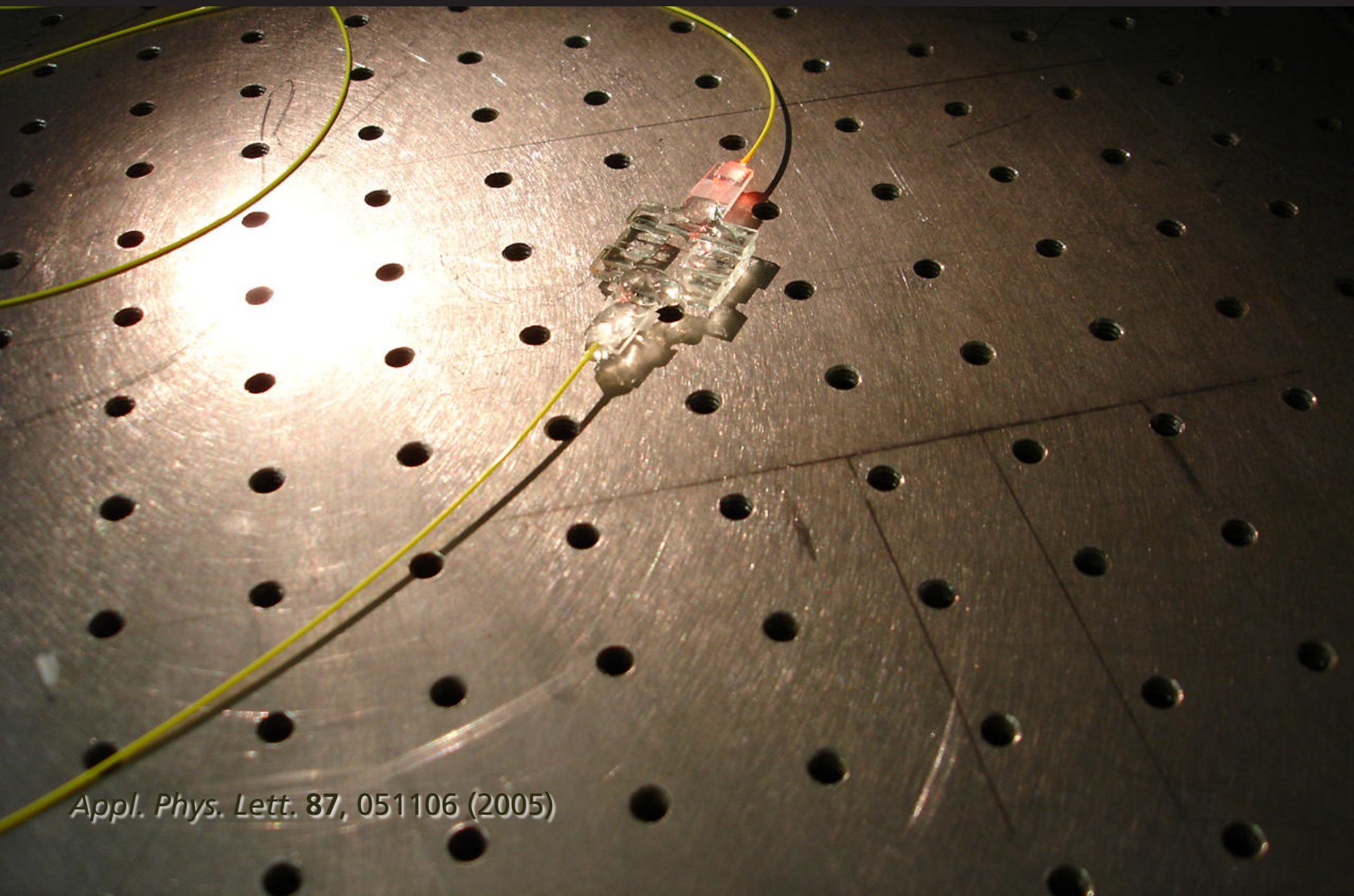
# Challenge

**failing to see problem as an *opportunity***

# Introduction

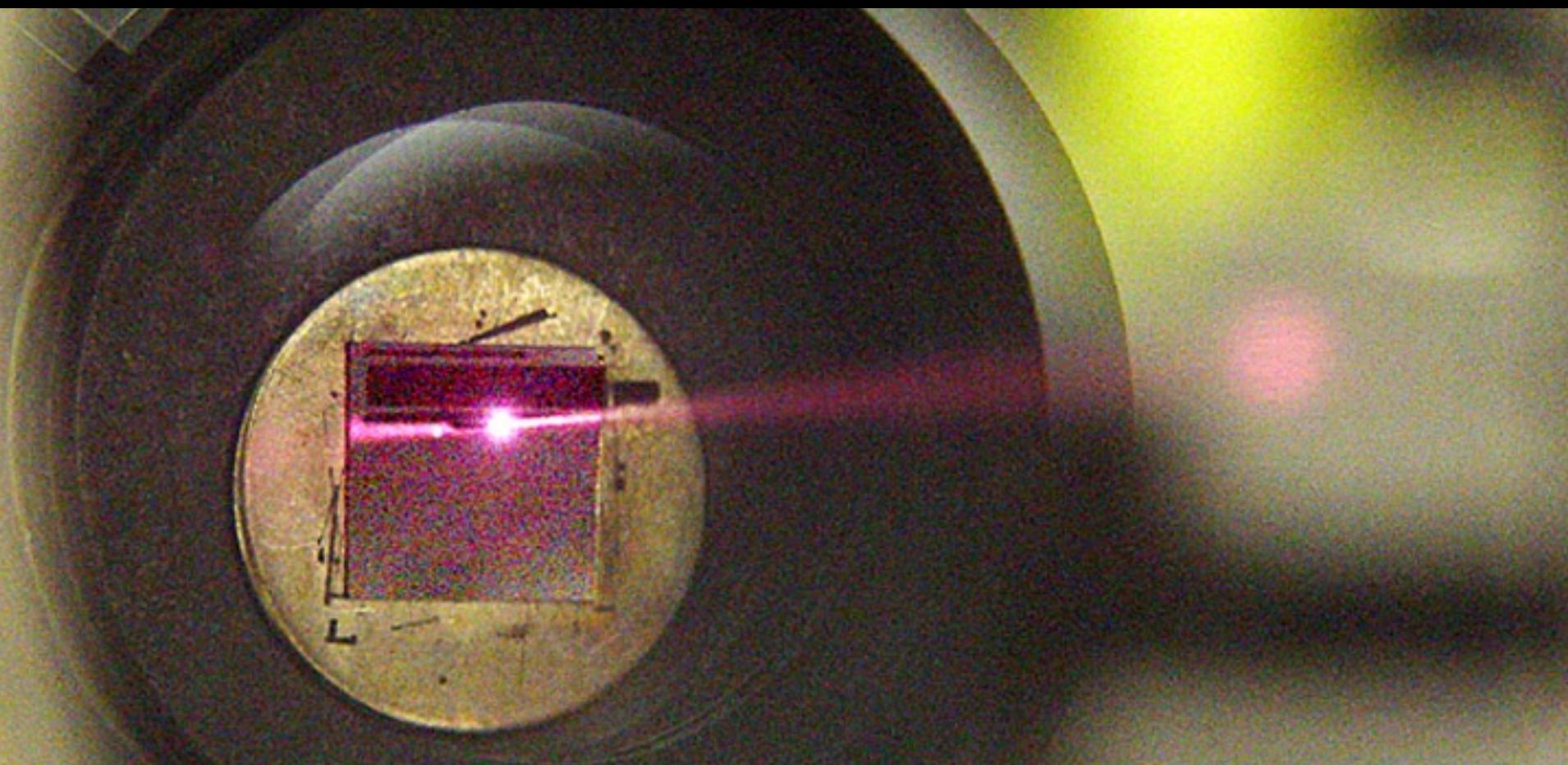


# Introduction

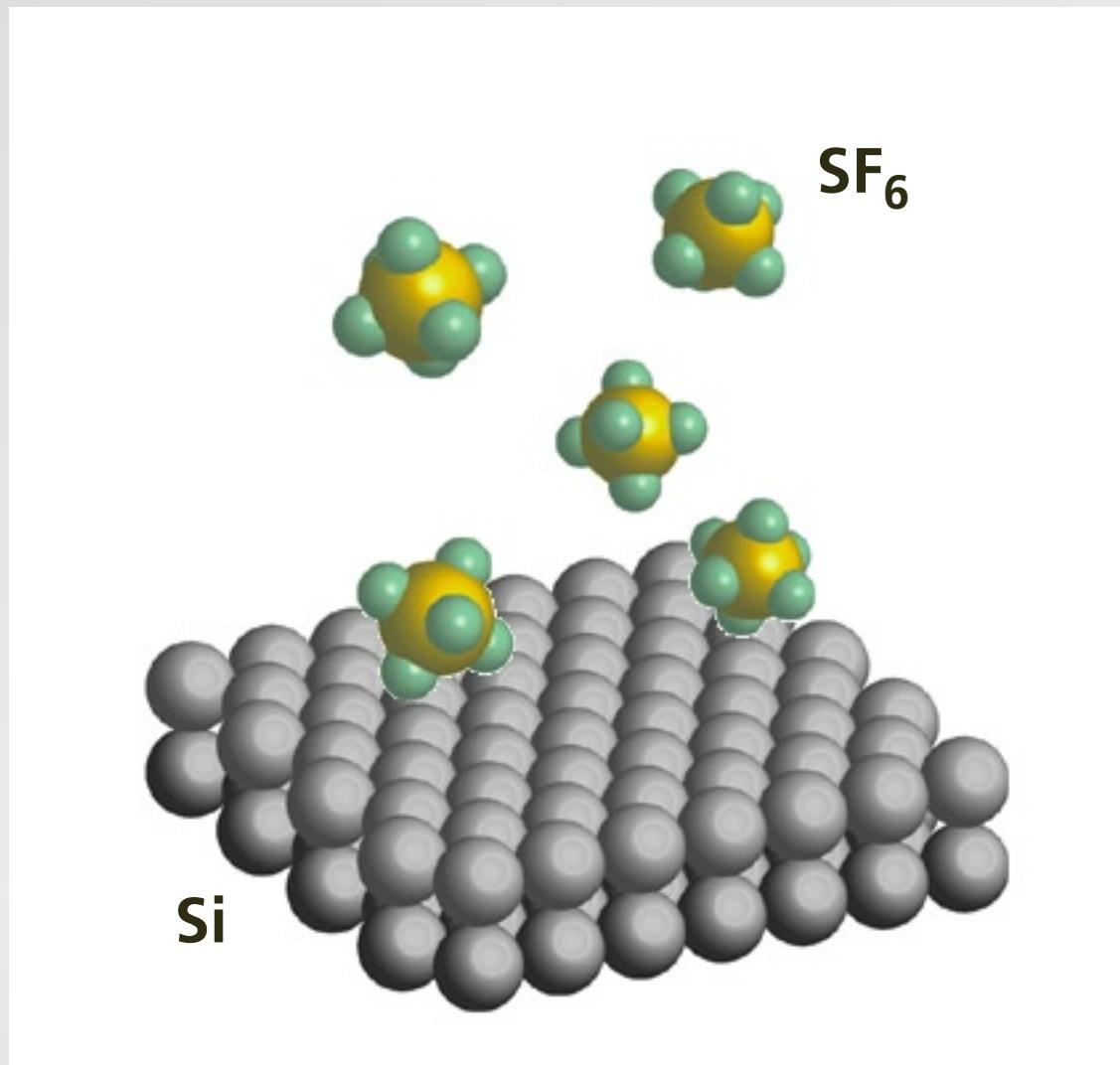


*Appl. Phys. Lett.* **87**, 051106 (2005)

# Introduction

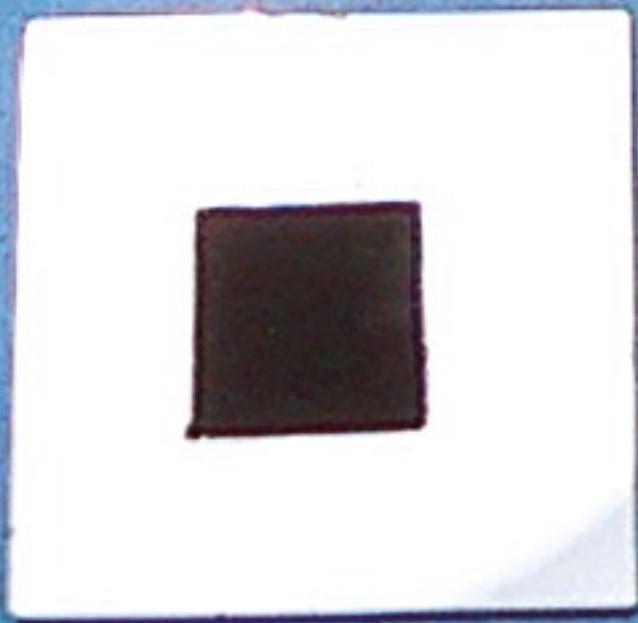


# Introduction



irradiate with 100-fs 10 kJ/m<sup>2</sup> pulses

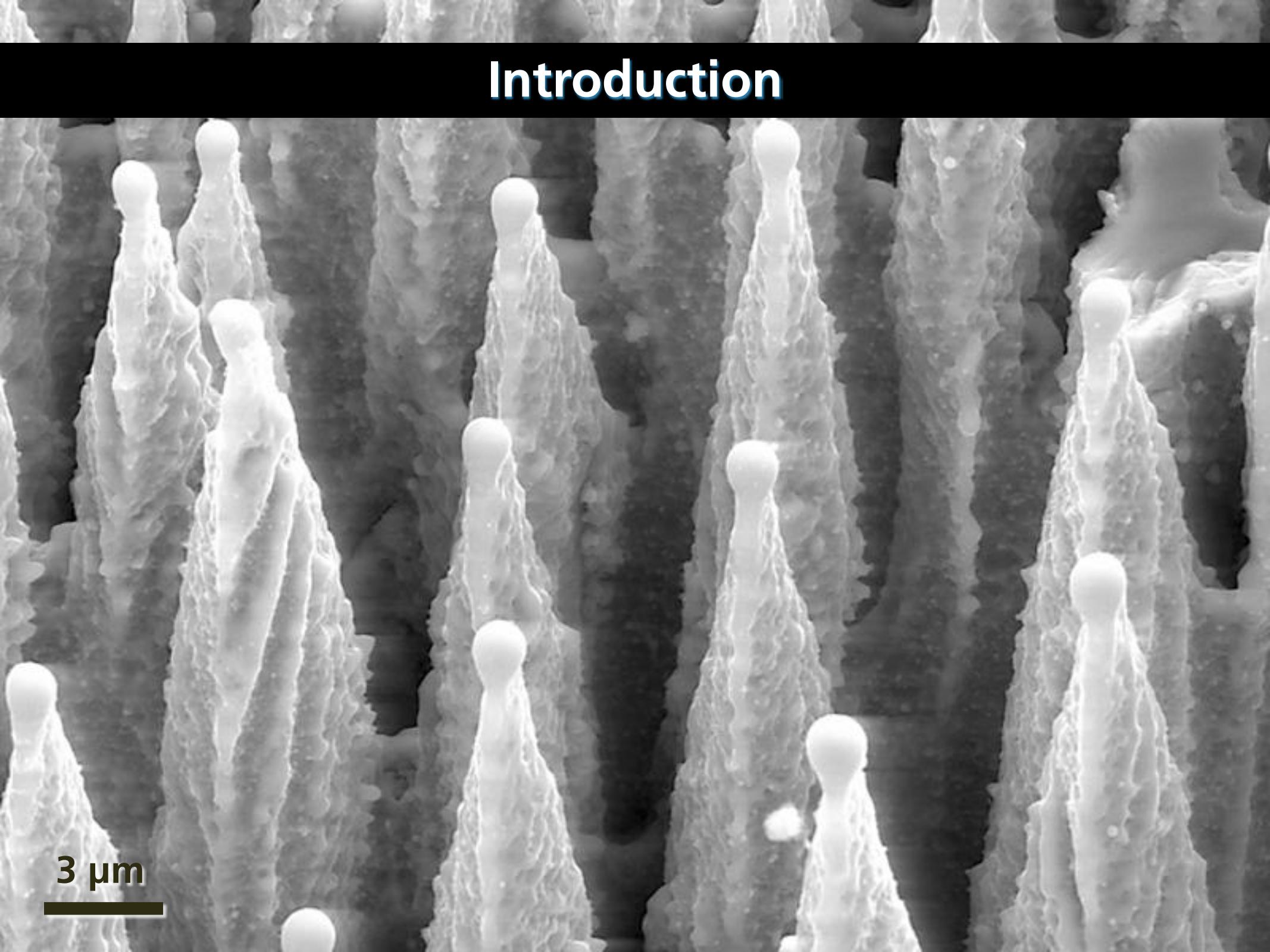
# Introduction



**“black silicon”**

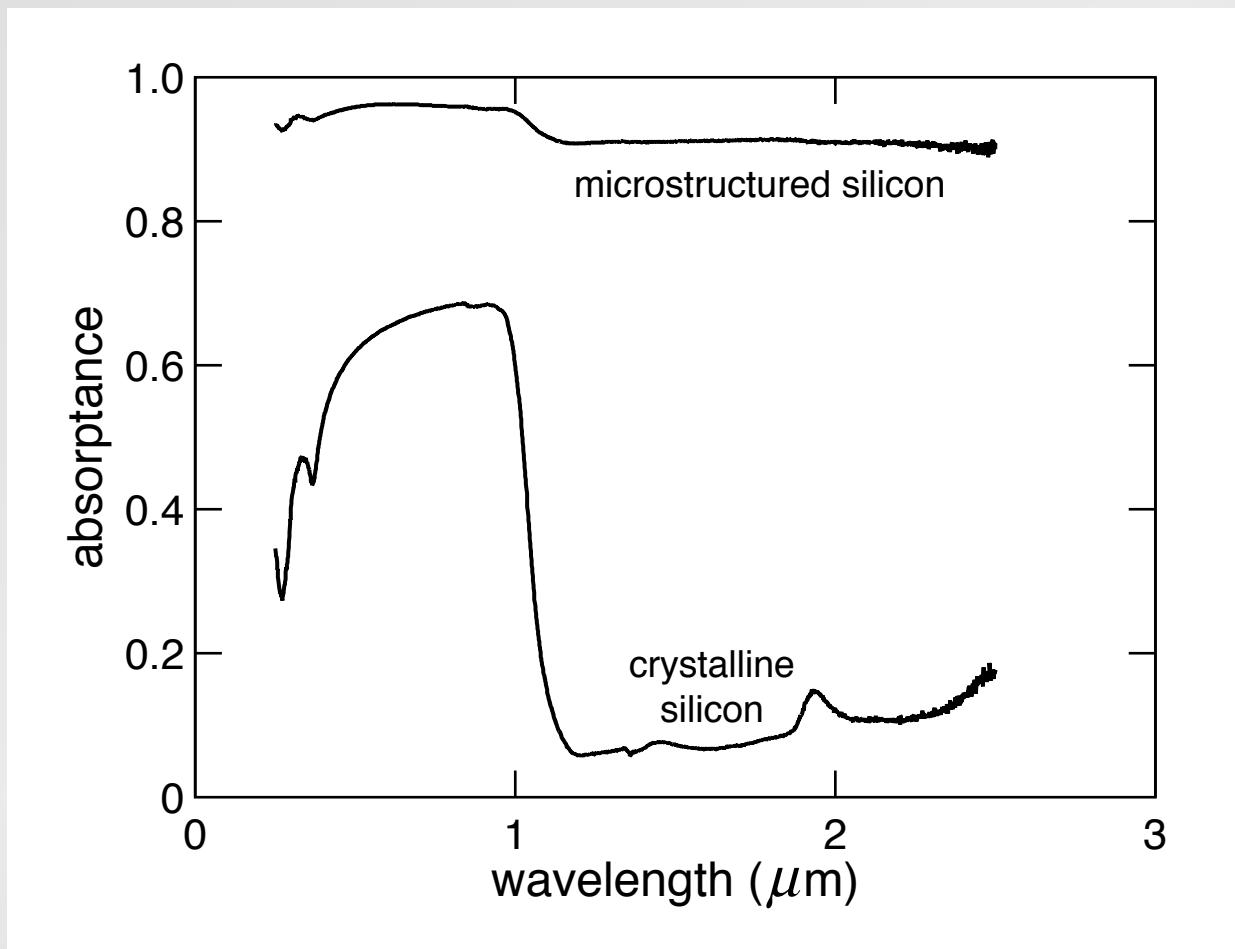


# Introduction

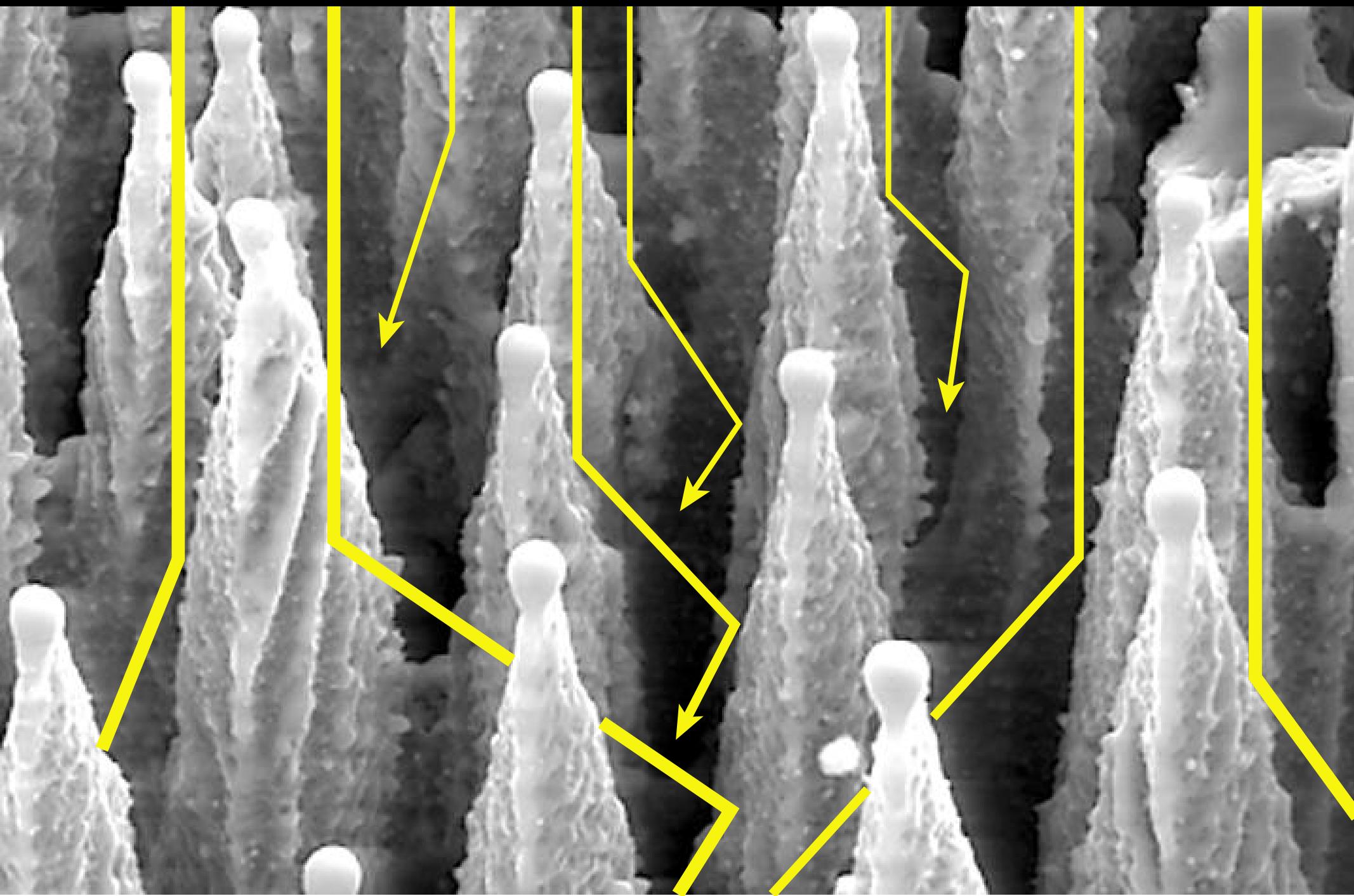


# Properties

absorptance ( $1 - R - T$ )

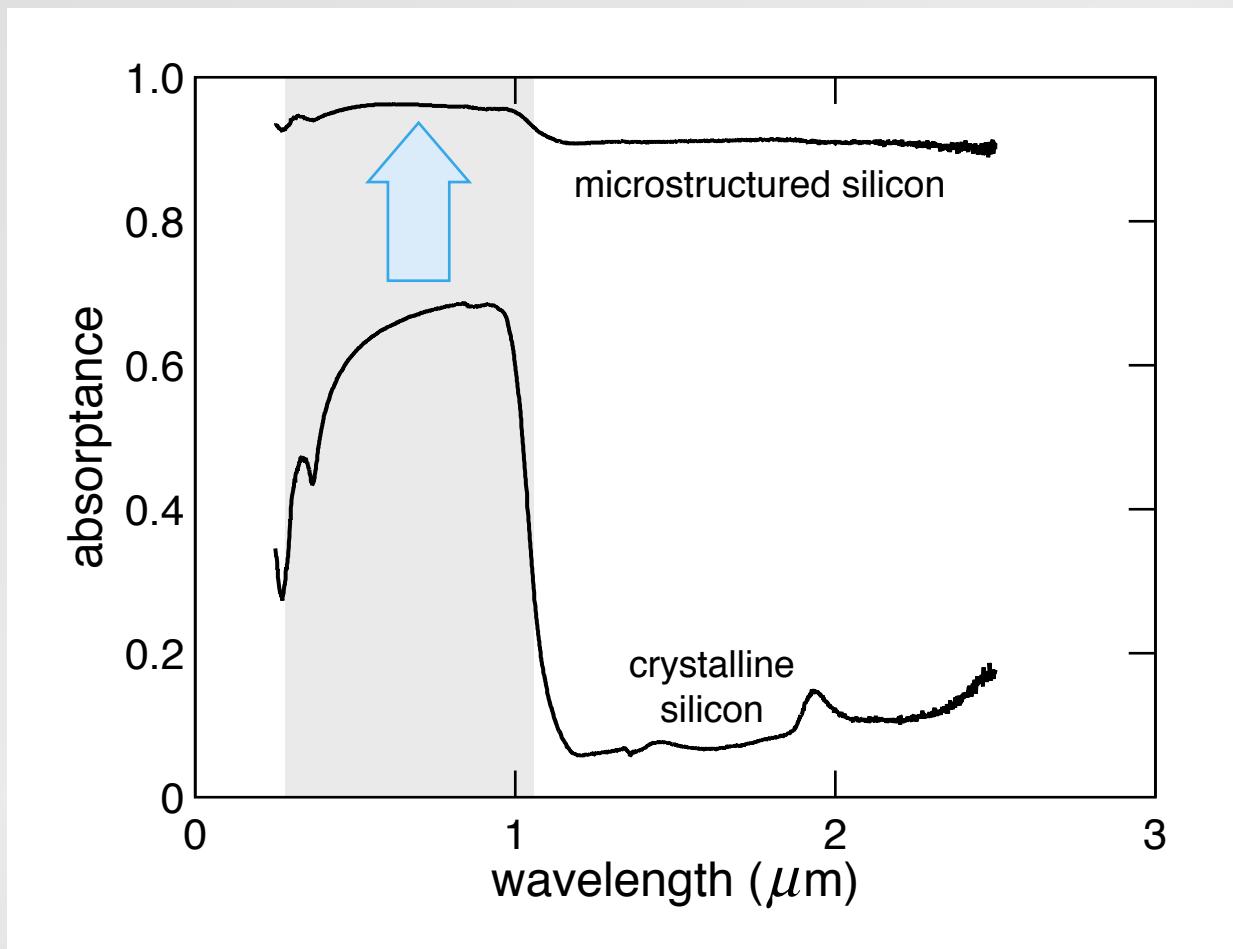


# Properties



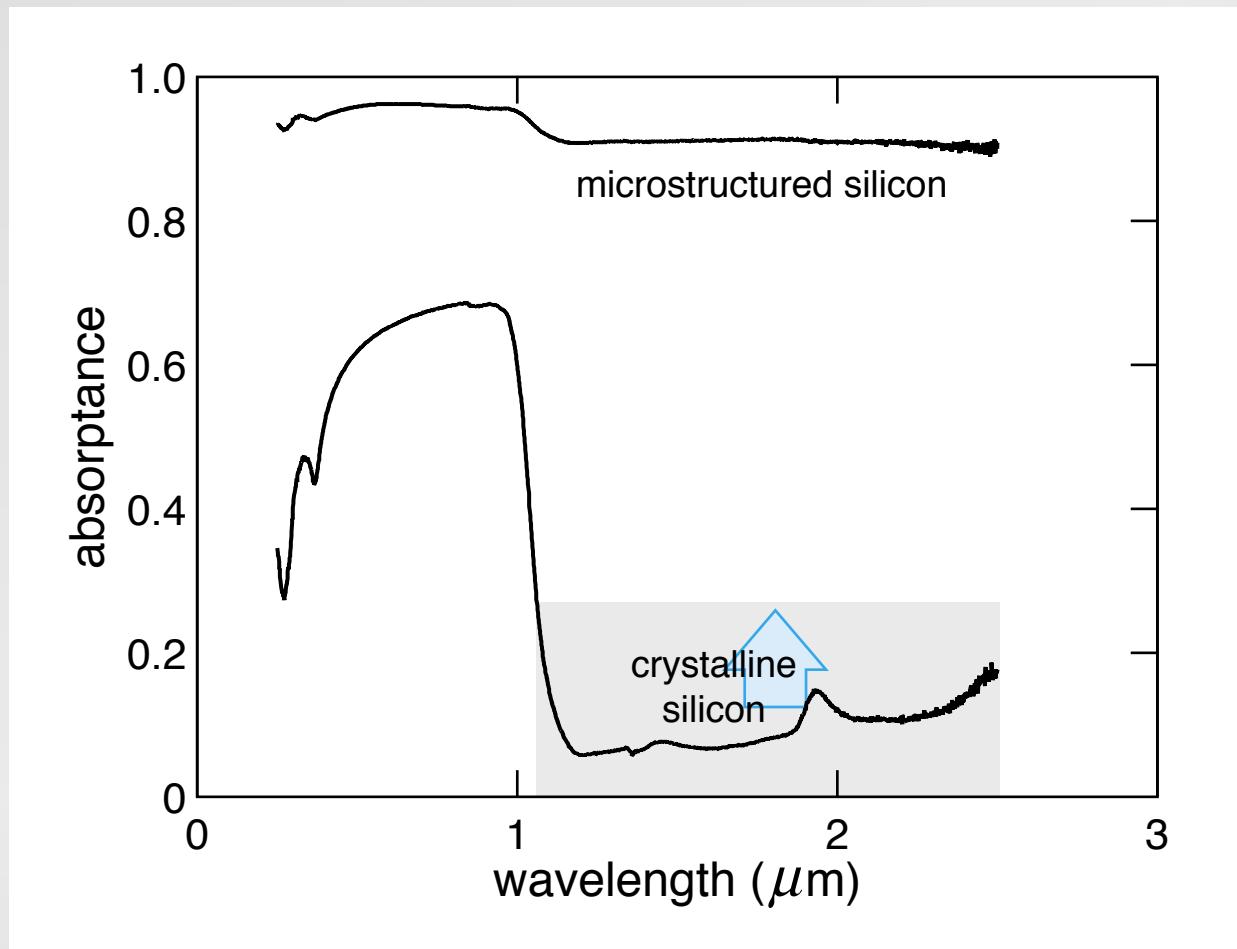
# Properties

multiple reflections enhance absorption



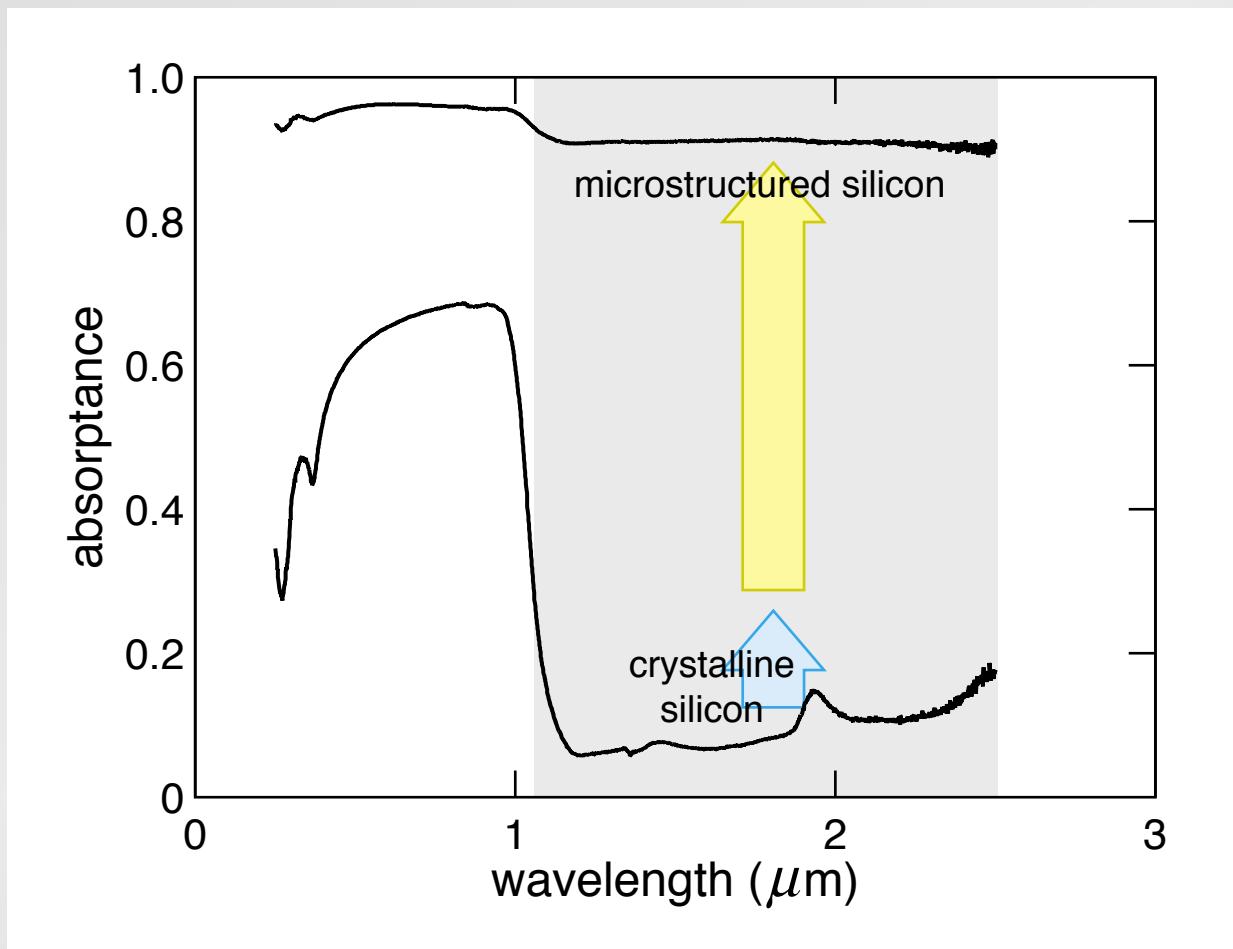
# Properties

multiple reflections enhance absorption

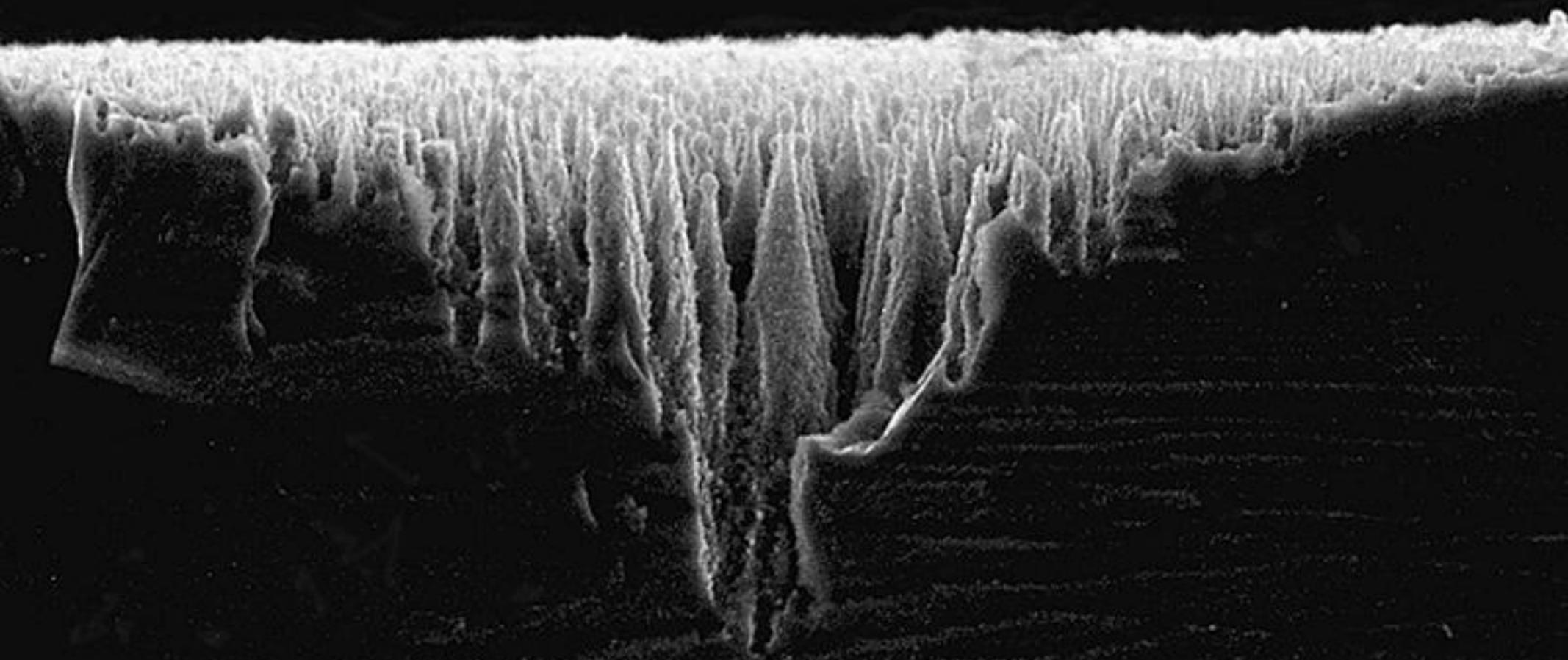


# Properties

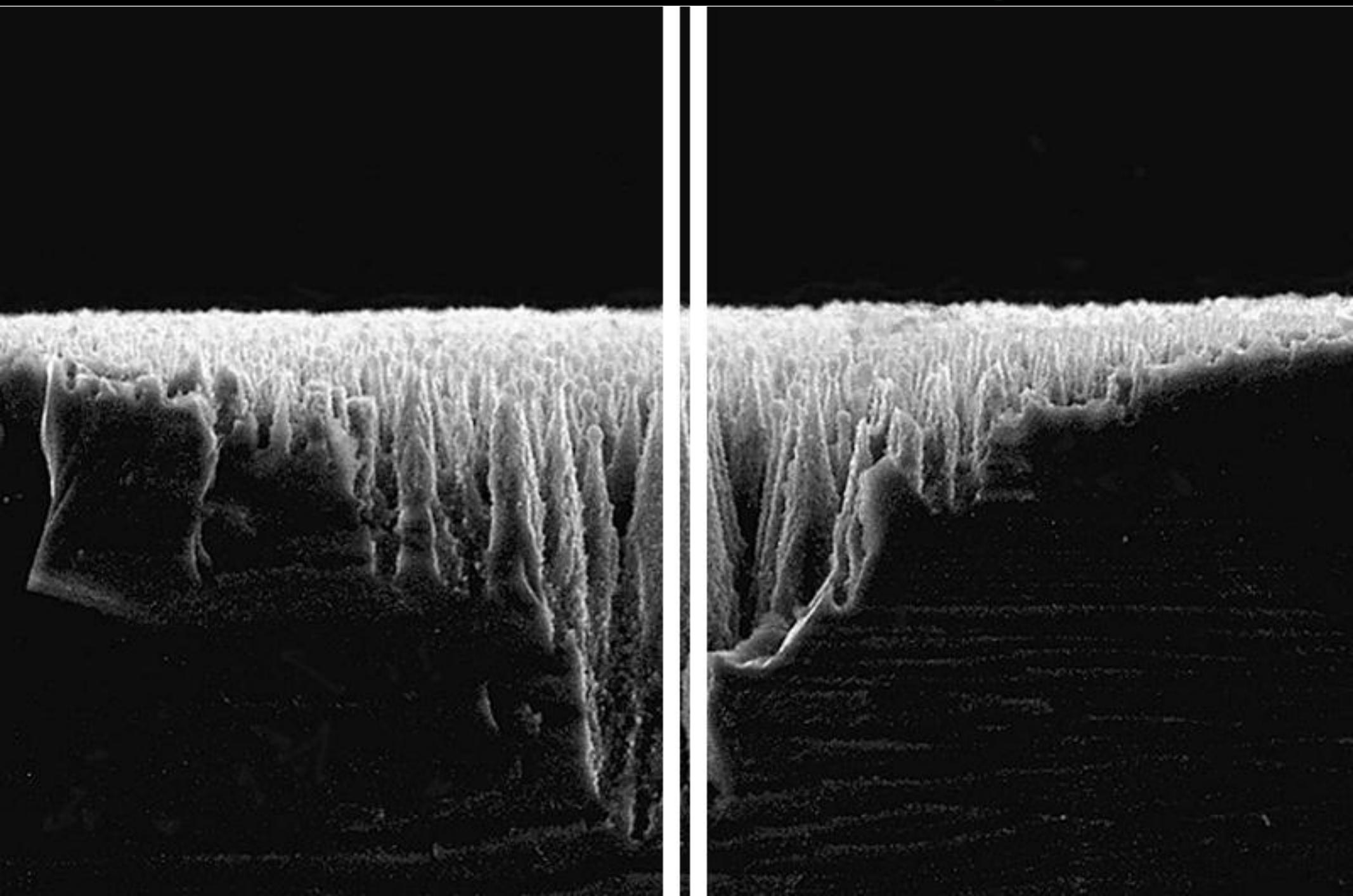
## electronic band structure changes



# Structural and chemical analysis



# Structural and chemical analysis



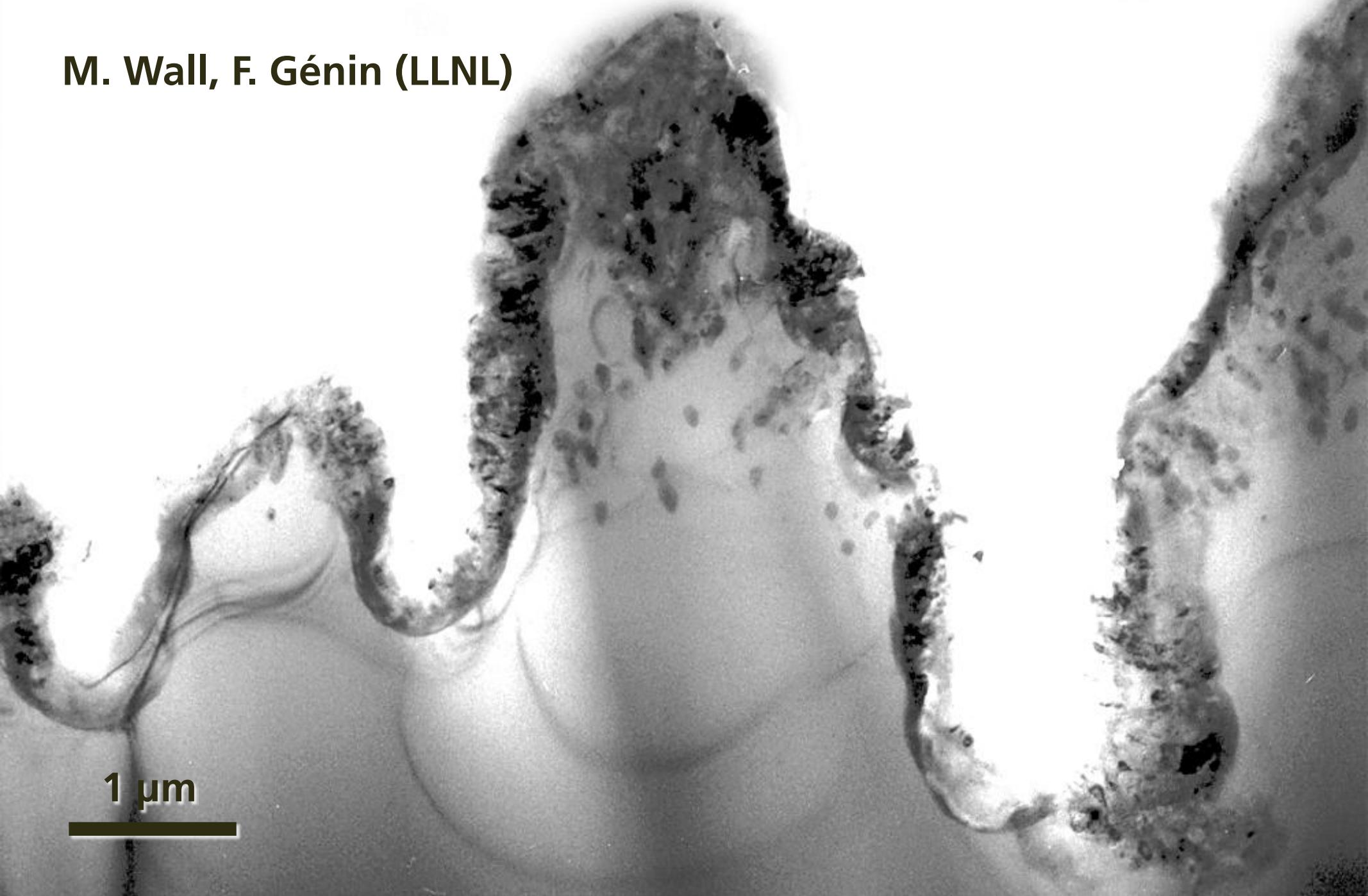
# **Structural and chemical analysis**

**cross-sectional  
Transmission Electron  
Microscopy**



# Structural and chemical analysis

M. Wall, F. Génin (LLNL)



1  $\mu\text{m}$

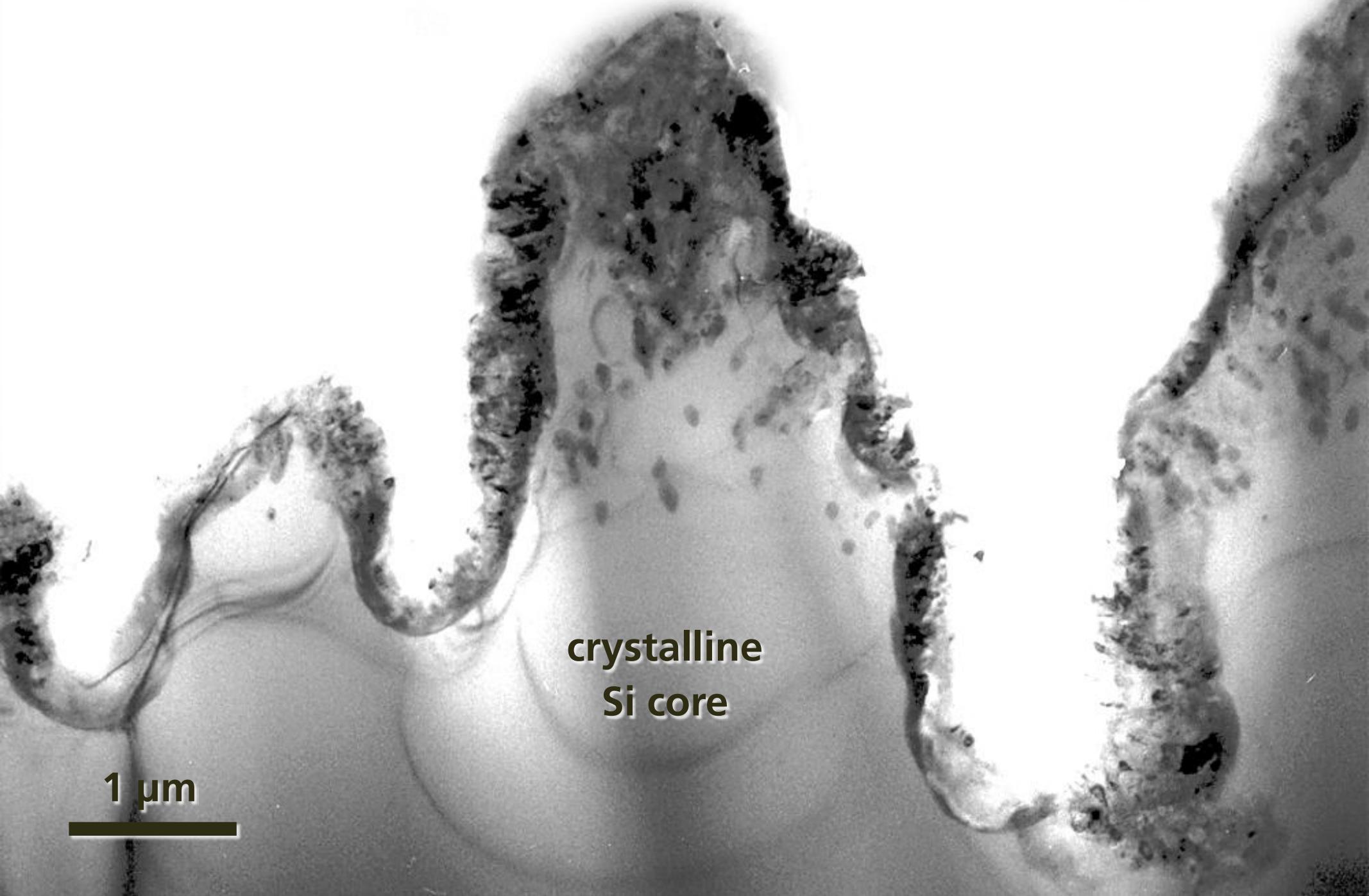
# Structural and chemical analysis

disordered  
surface layer

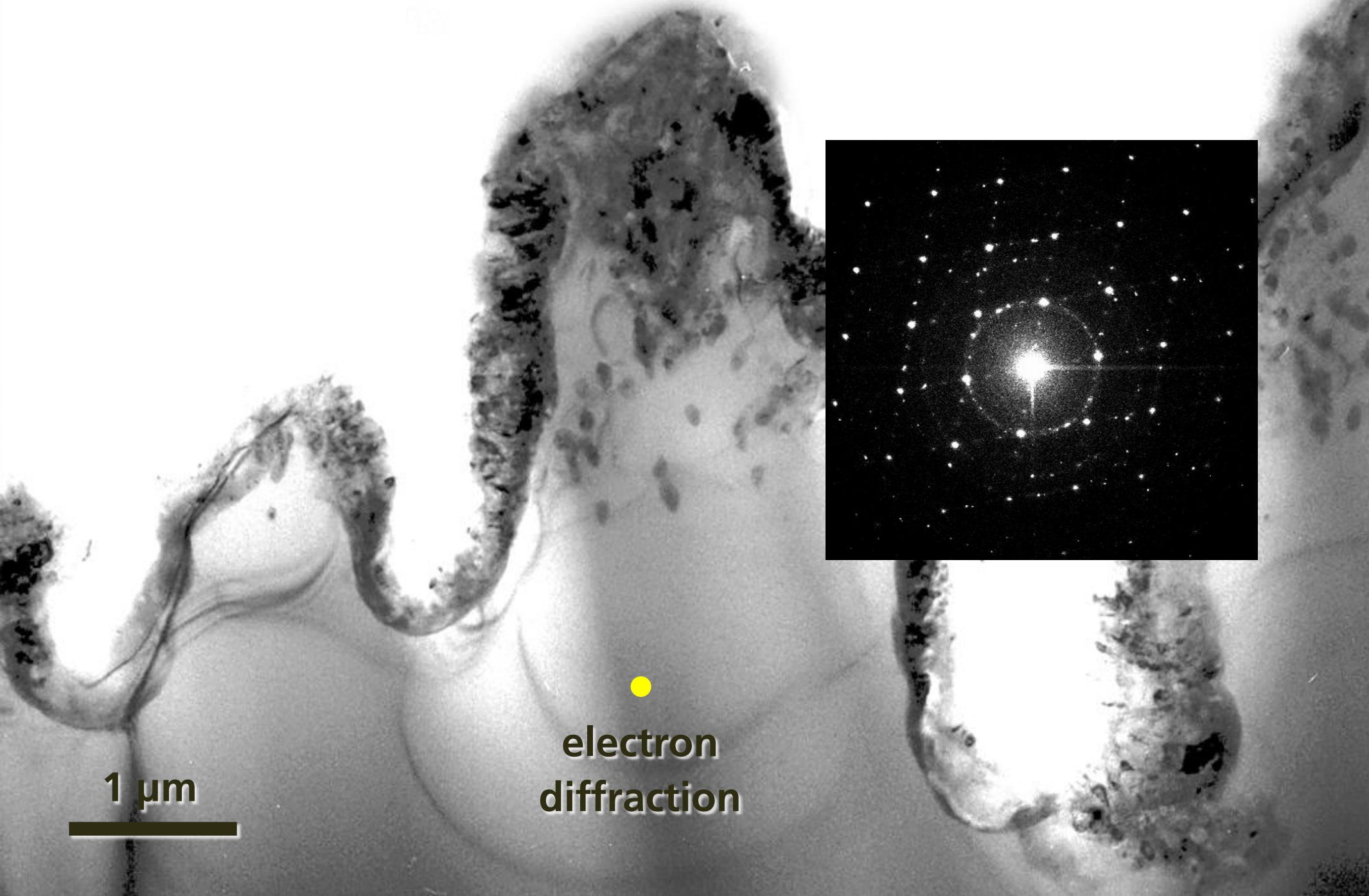


1  $\mu\text{m}$

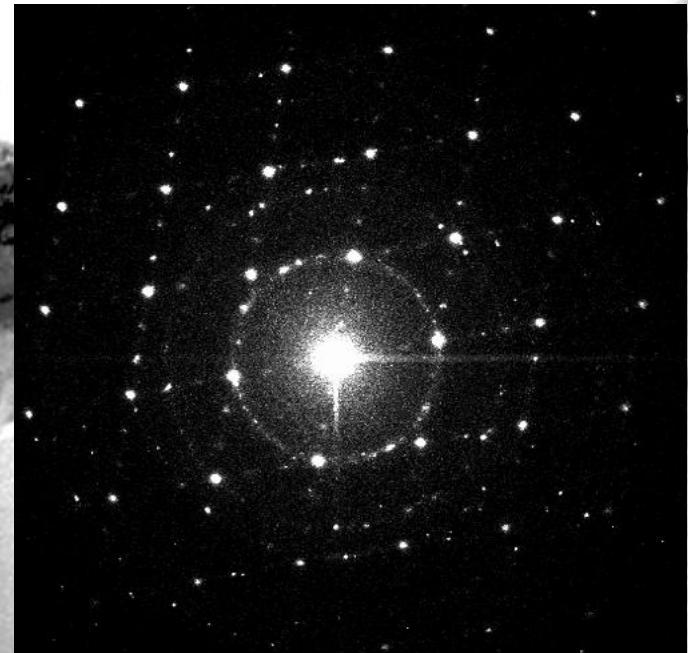
# Structural and chemical analysis



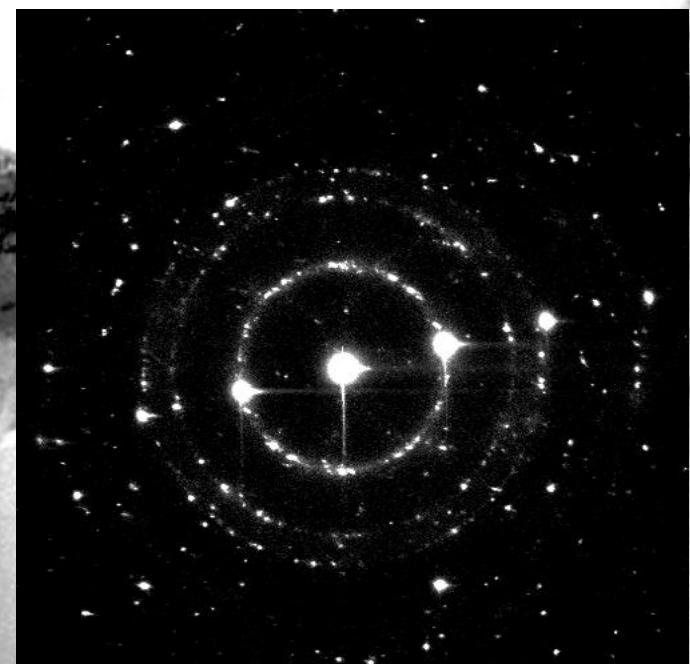
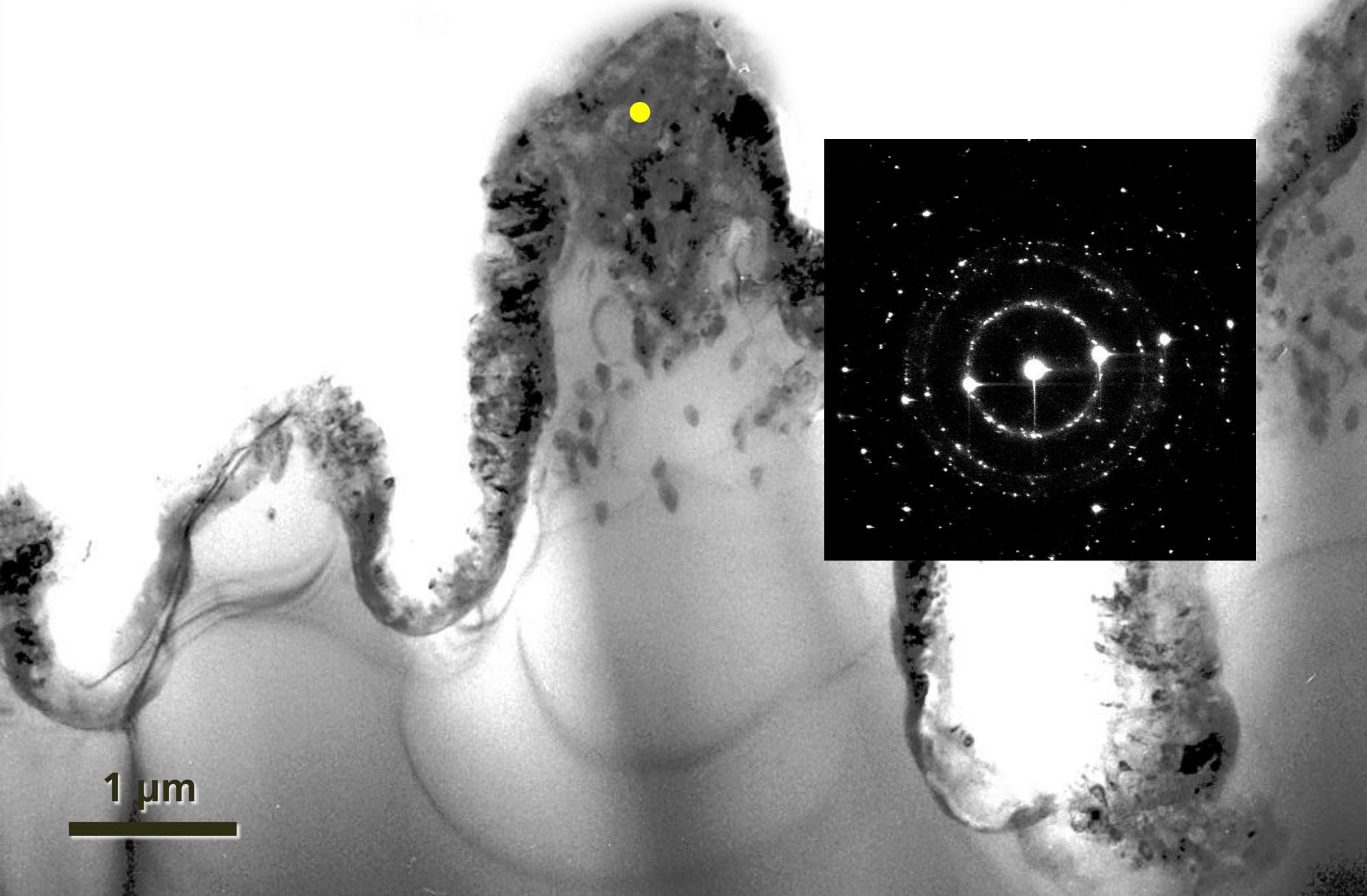
# Structural and chemical analysis



electron  
diffraction



# Structural and chemical analysis



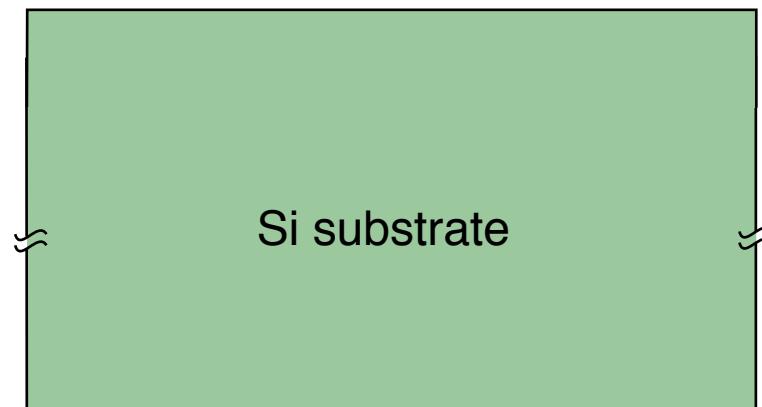
# Structural and chemical analysis

- 300-nm disordered surface layer
- undisturbed crystalline core
- surface layer: polycrystalline Si with 1.6% sulfur

1  $\mu\text{m}$

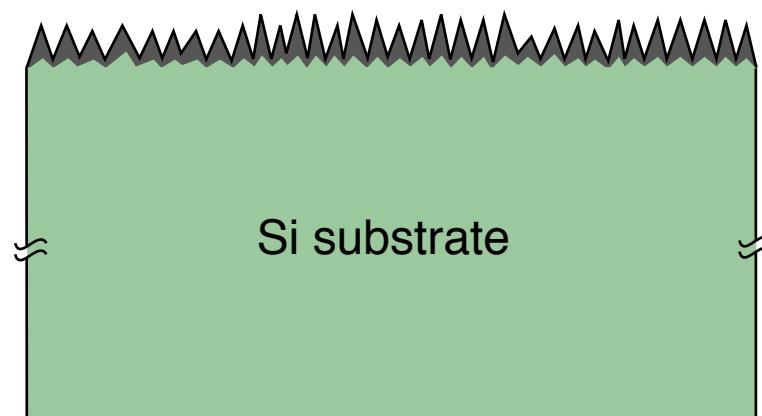
# Detectors

## black silicon/silicon junction



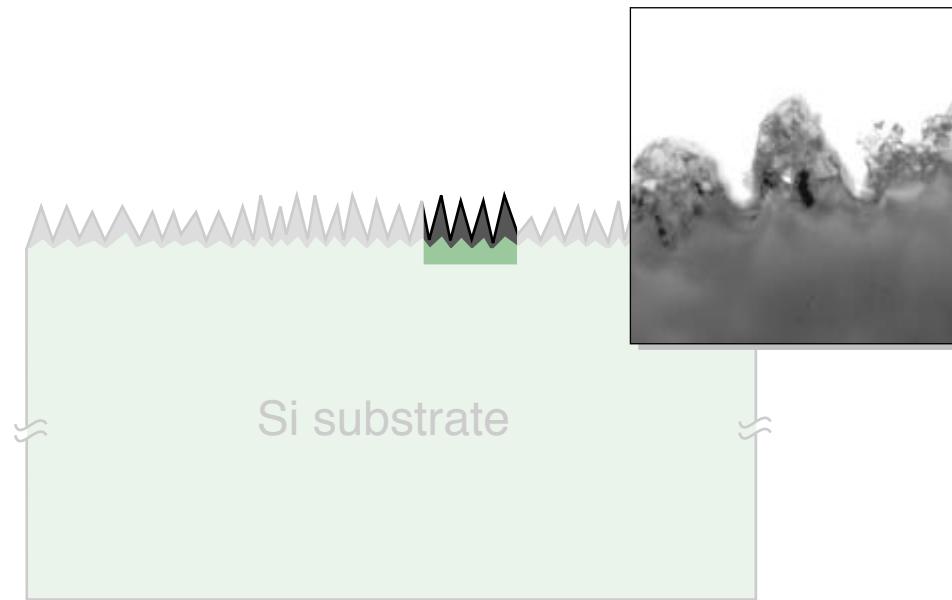
# Detectors

## black silicon/silicon junction



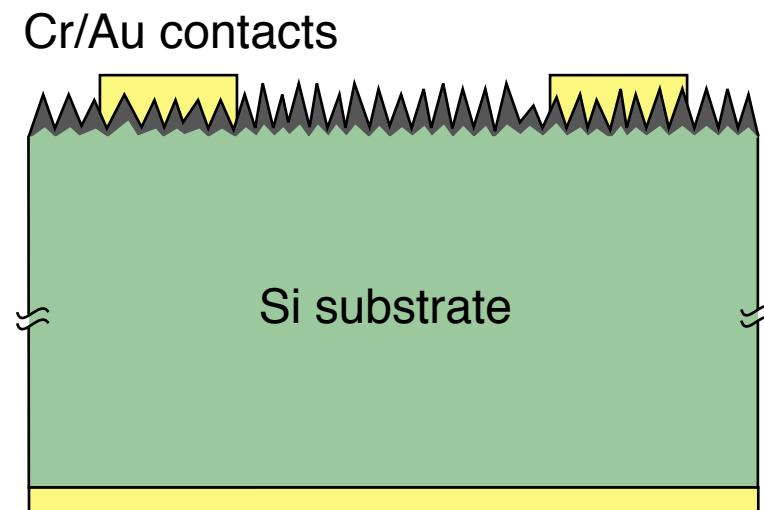
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## black silicon/silicon junction



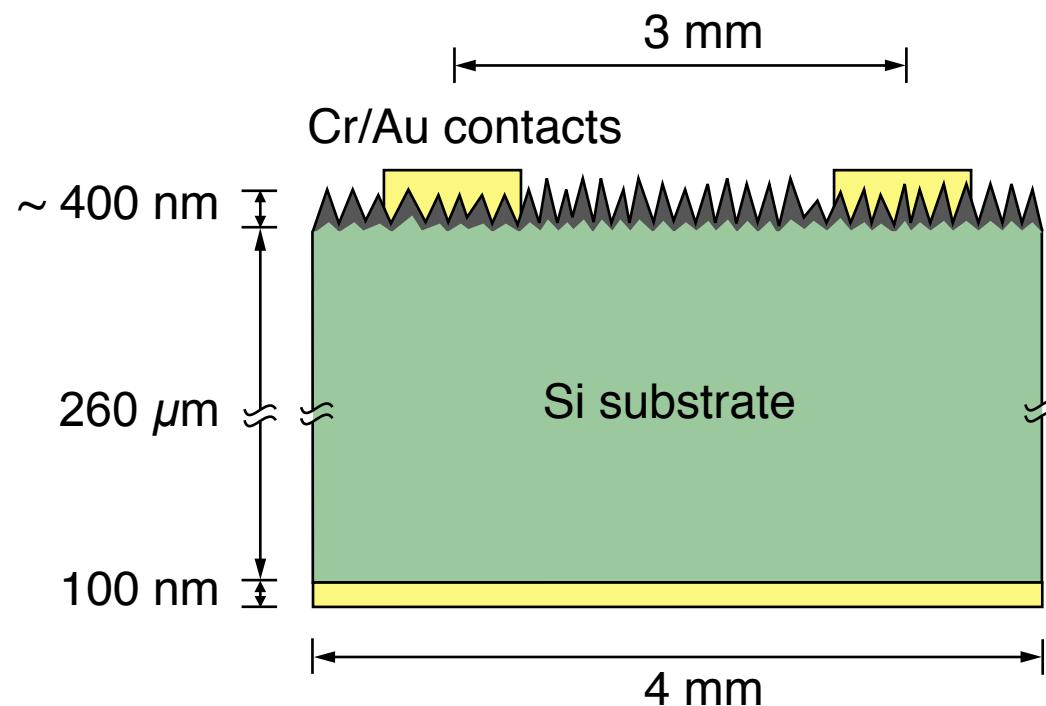
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## black silicon/silicon junction



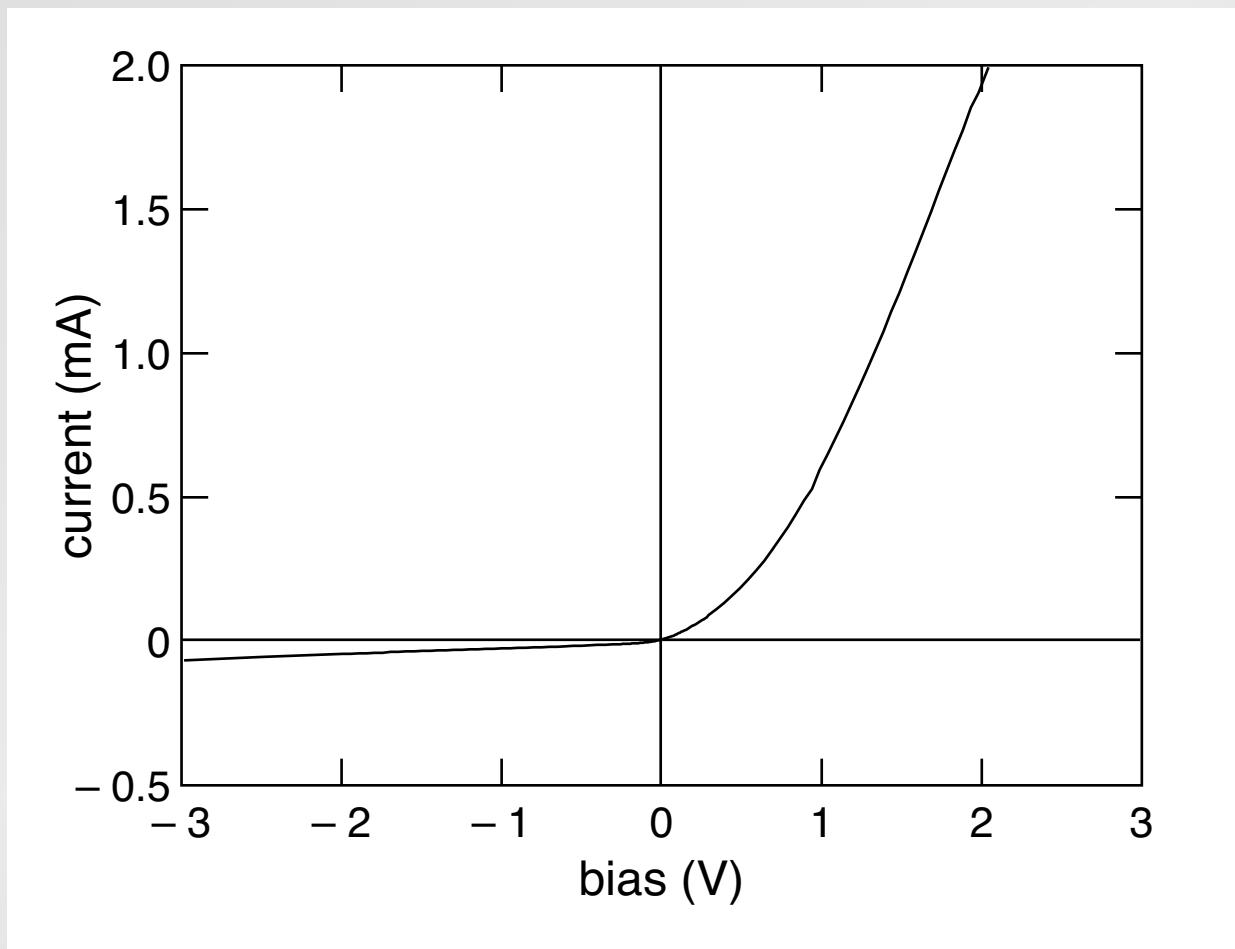
# Detectors

## black silicon/silicon junction



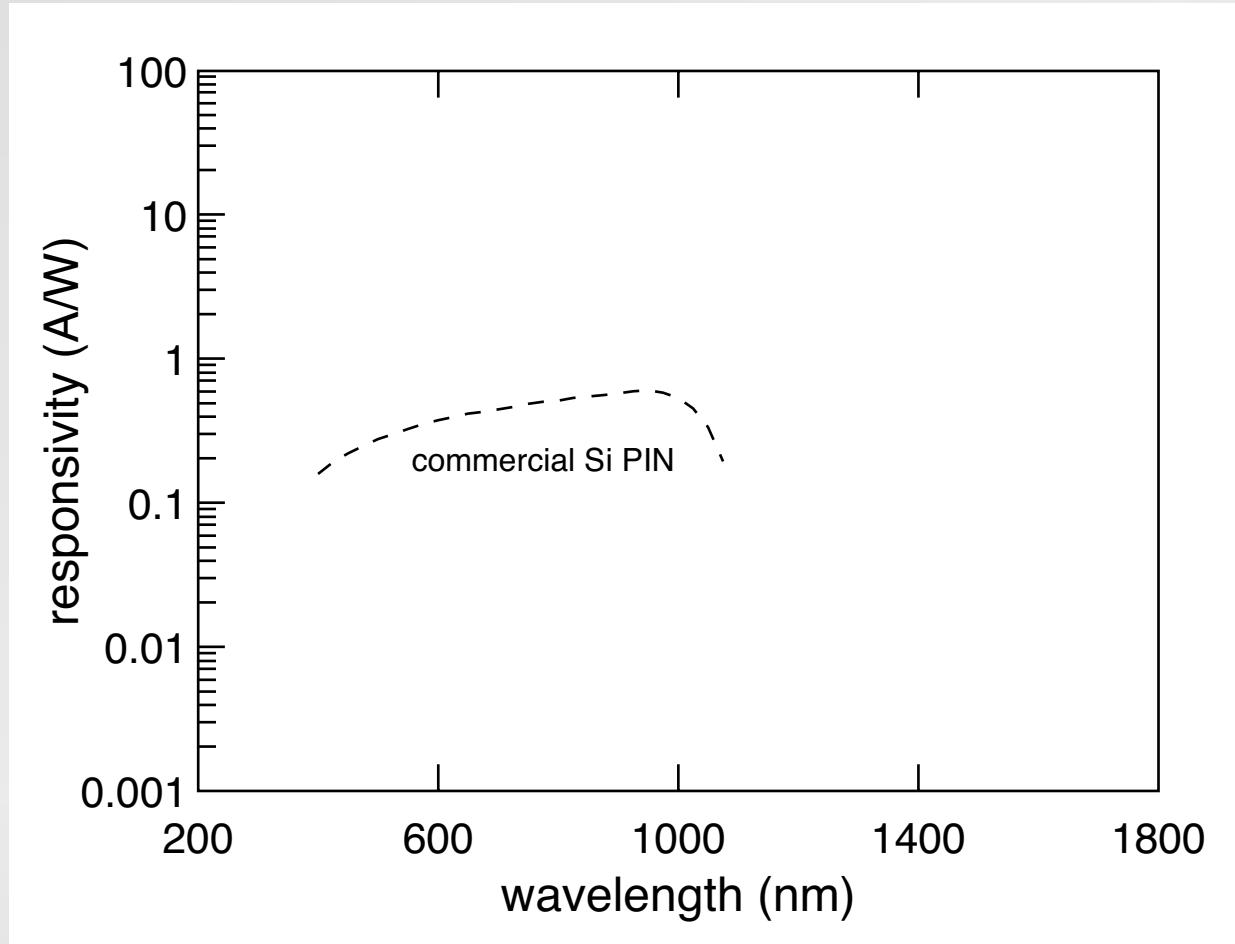
# Detectors

## *I/V characteristics*



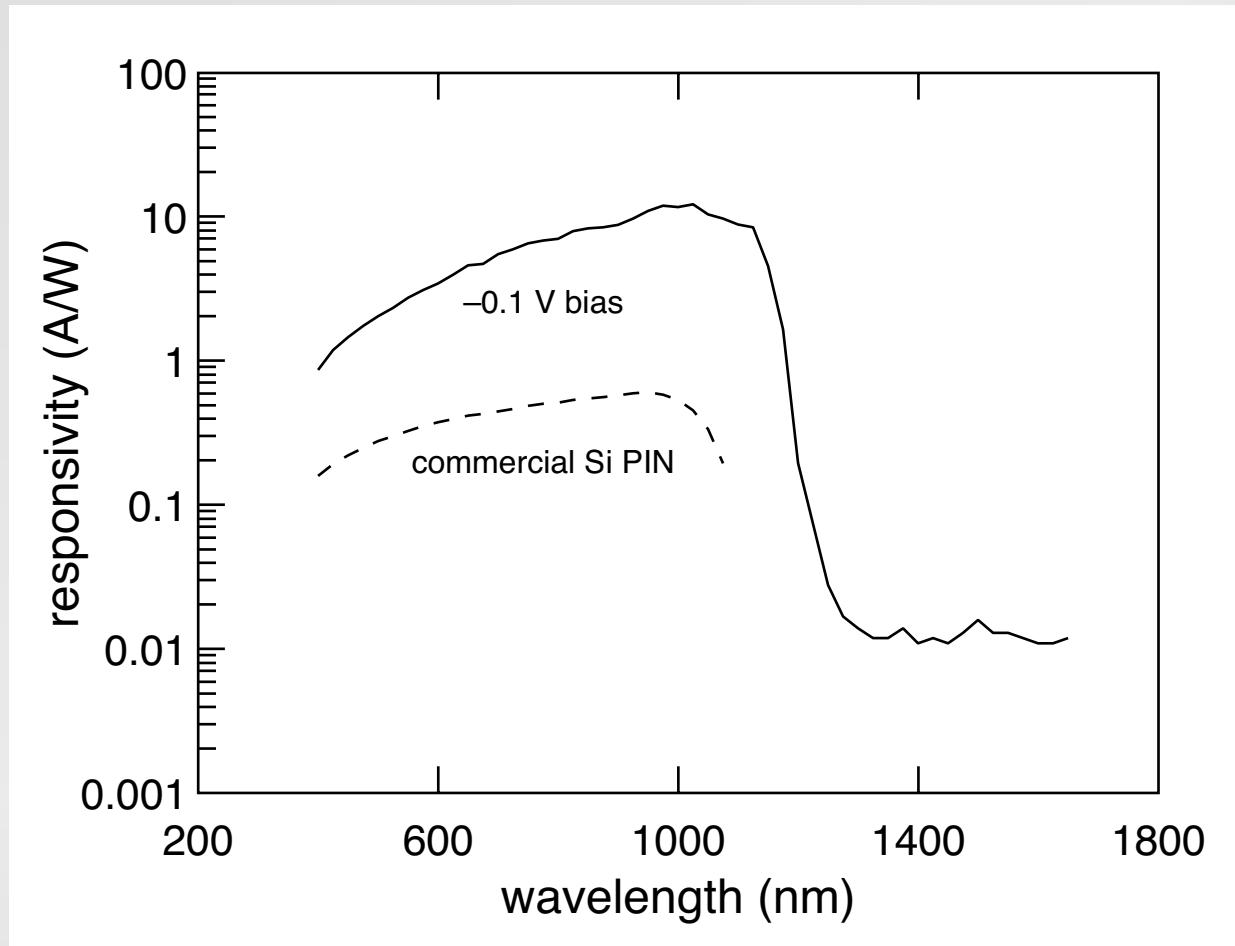
# Detectors

## responsivity



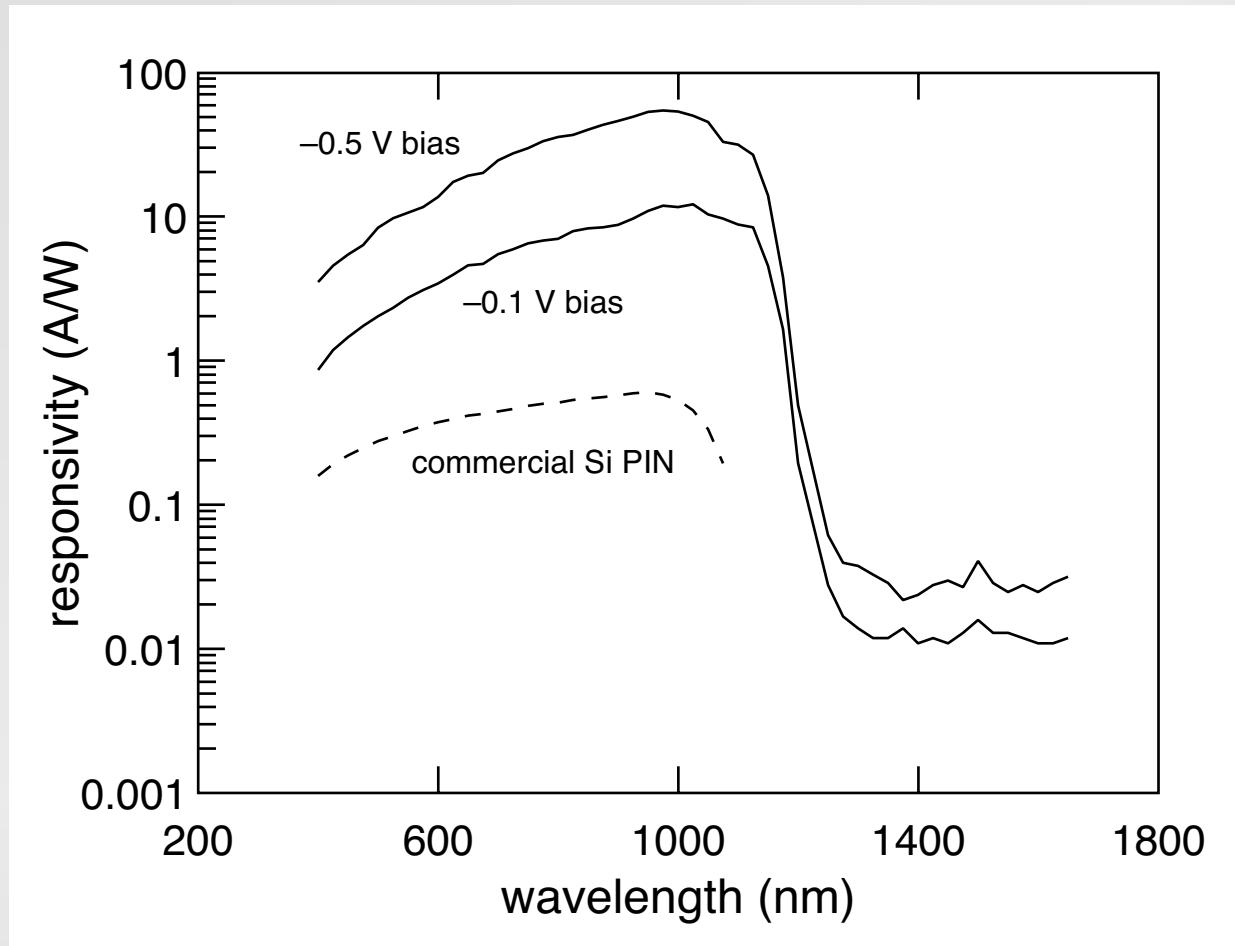
# Detectors

## responsivity



# Detectors

## responsivity

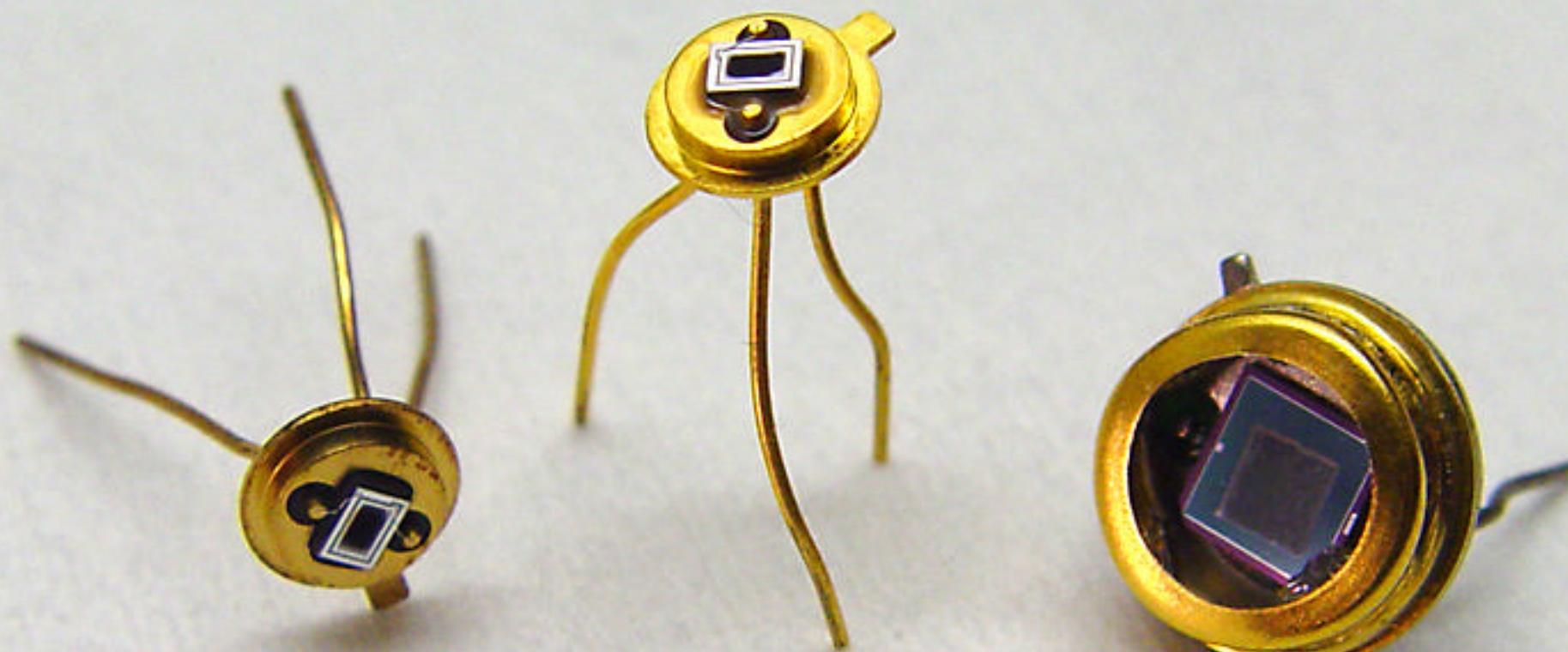


# Detectors

Black silicon photodiode (at 0.5 V bias):

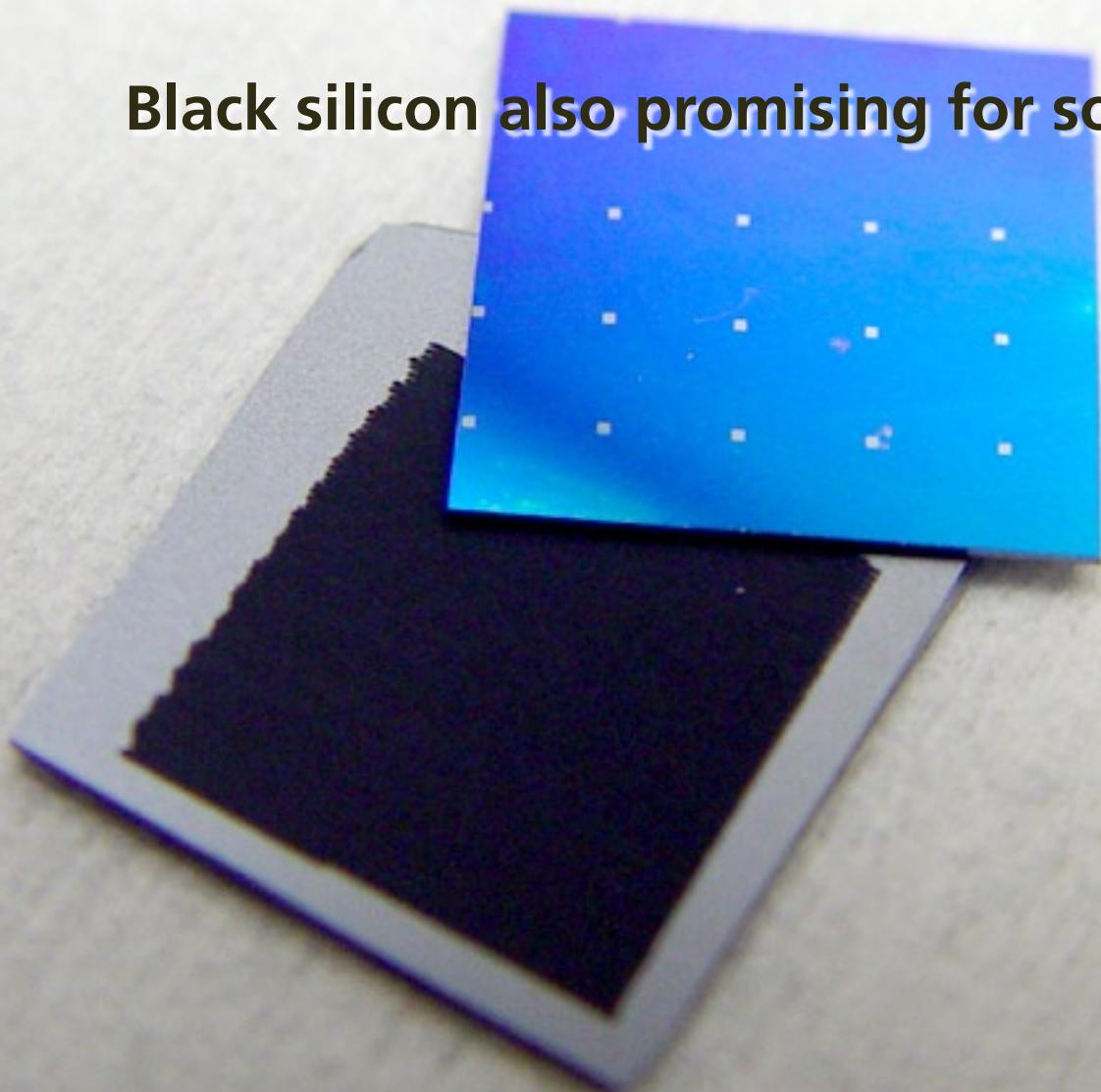
- 100x larger signal in visible (gain!)
- $10^5$  larger signal in infrared

# Detectors

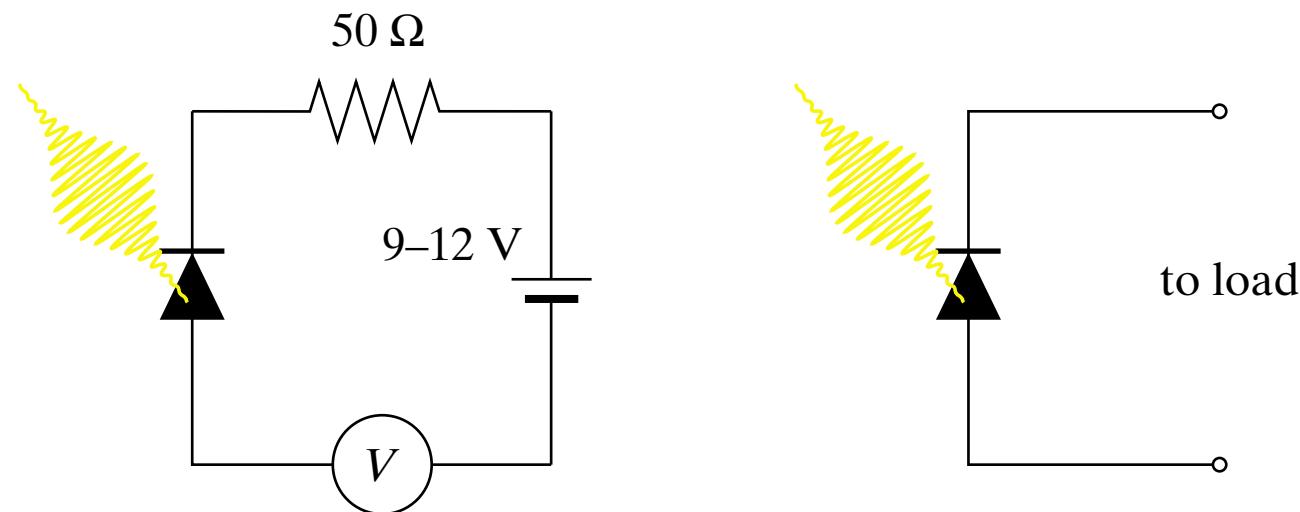


# Detectors

**Black silicon also promising for solar cells**

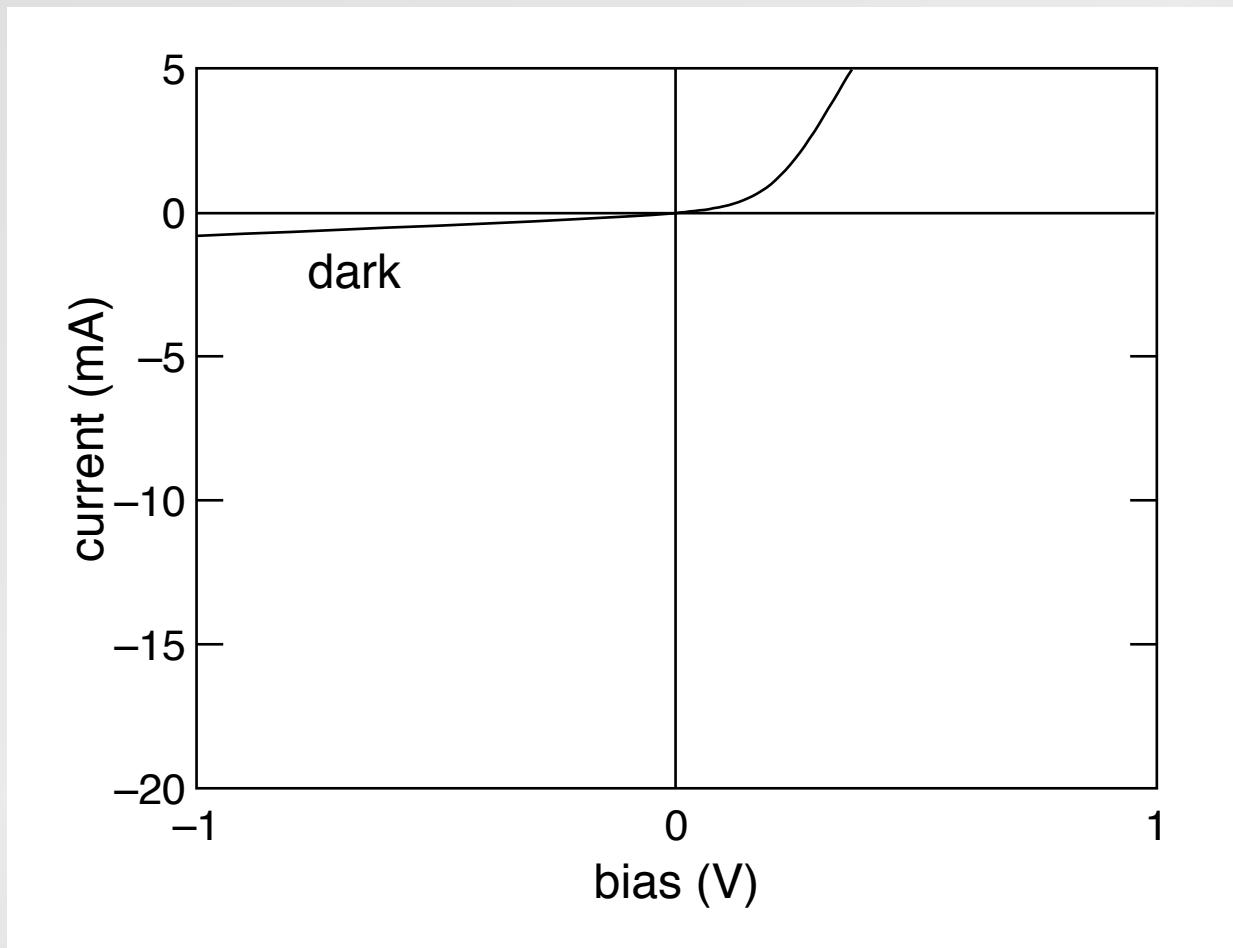


# Detectors



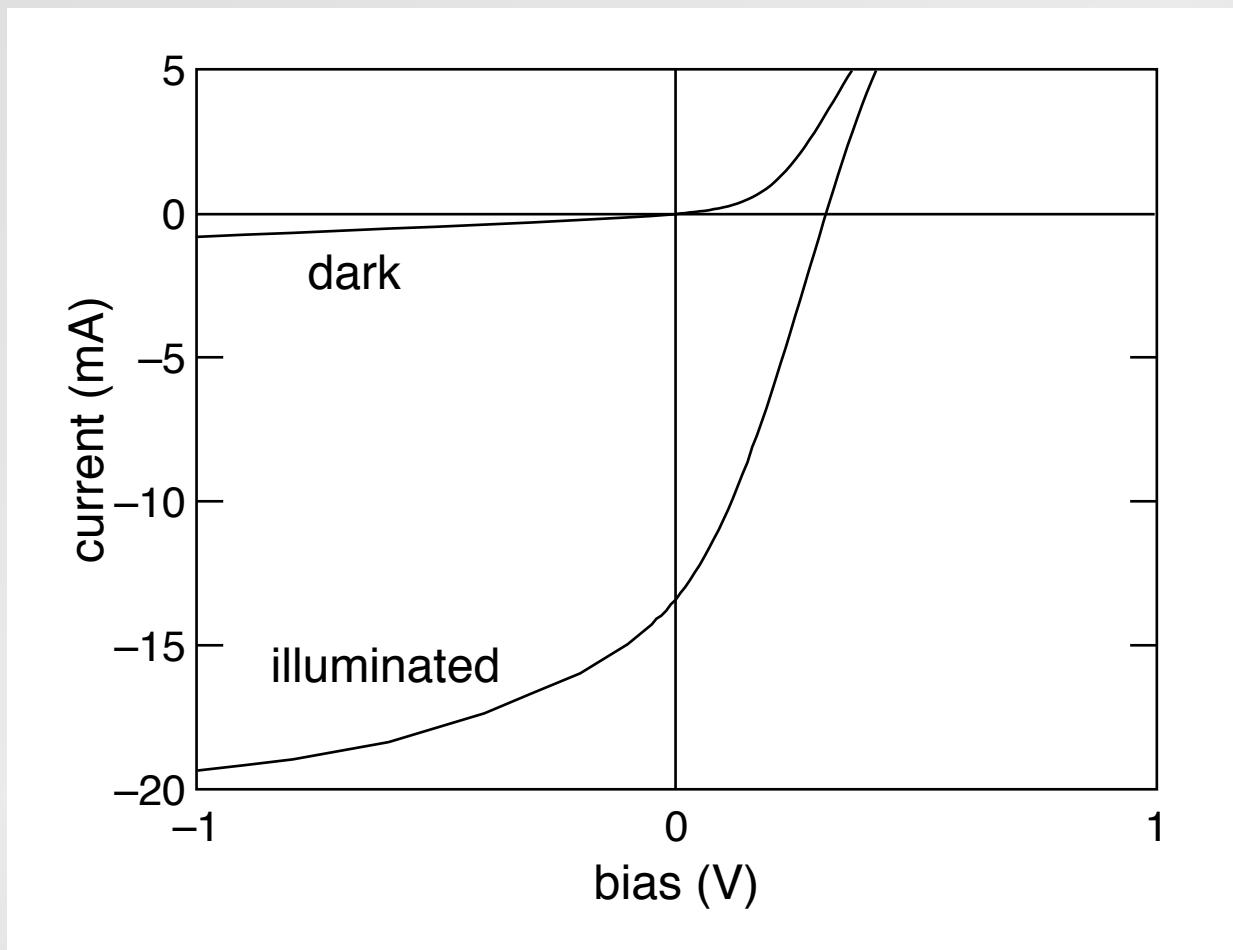
# Detectors

## *I/V characteristics*



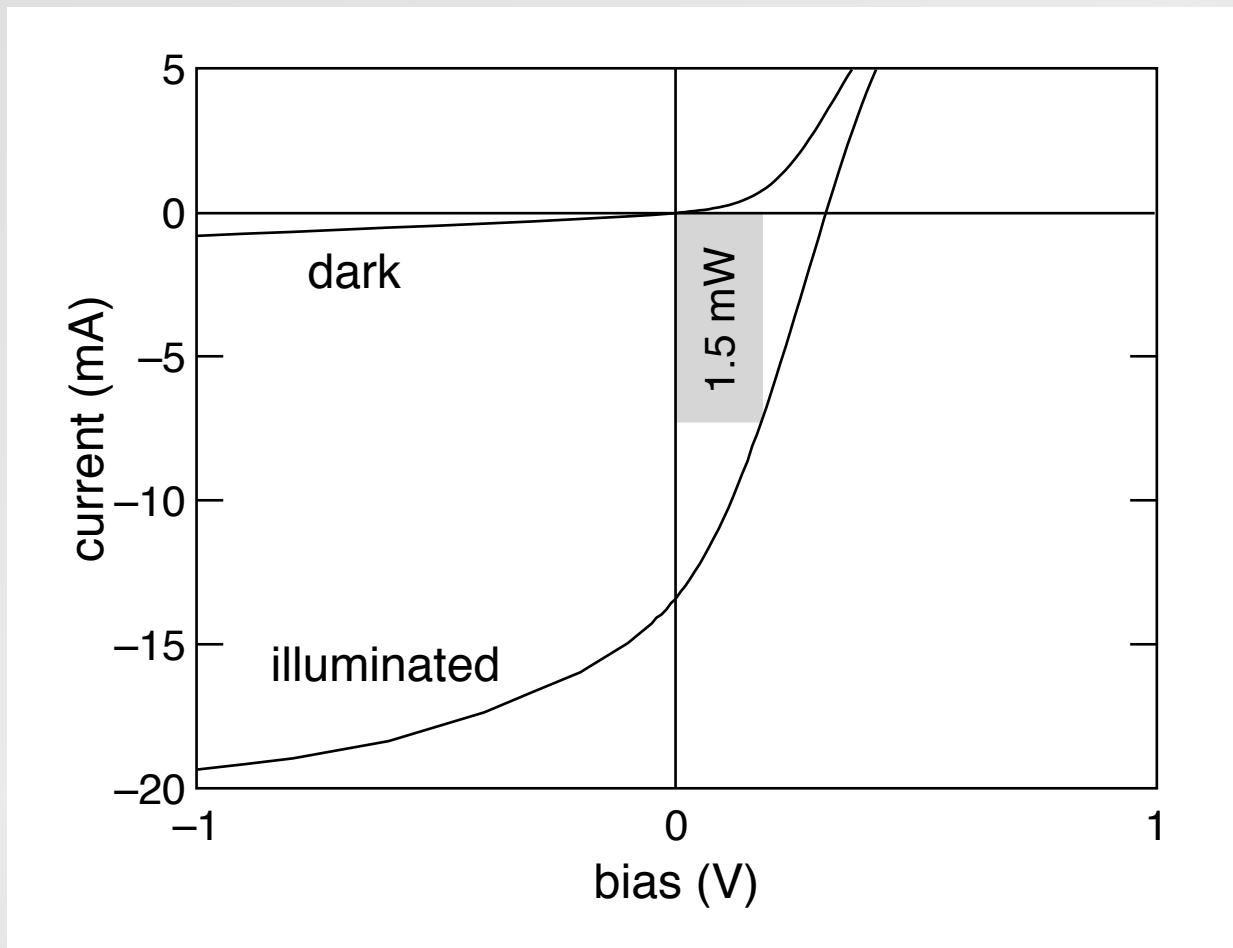
# Detectors

## *I/V* characteristics



# Detectors

## *I/V* characteristics



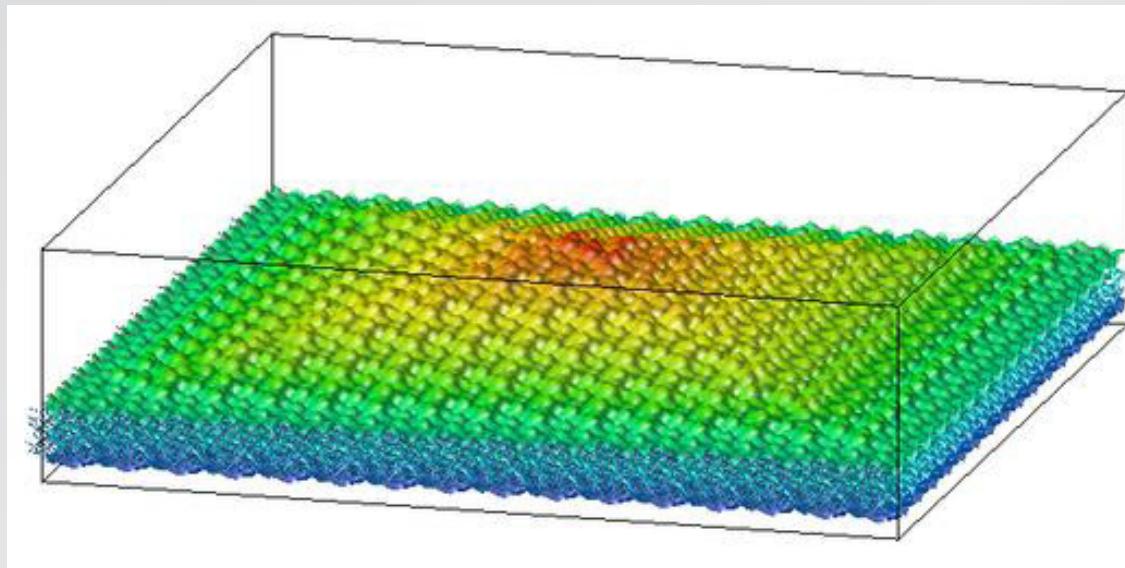
# Detectors

## **Black silicon solar cell (preliminary):**

- 2–3% efficiency
- photocurrent generated in thin layer

# Needs

**Understanding the resulting properties**



**full DFT code for very large numbers of atoms**

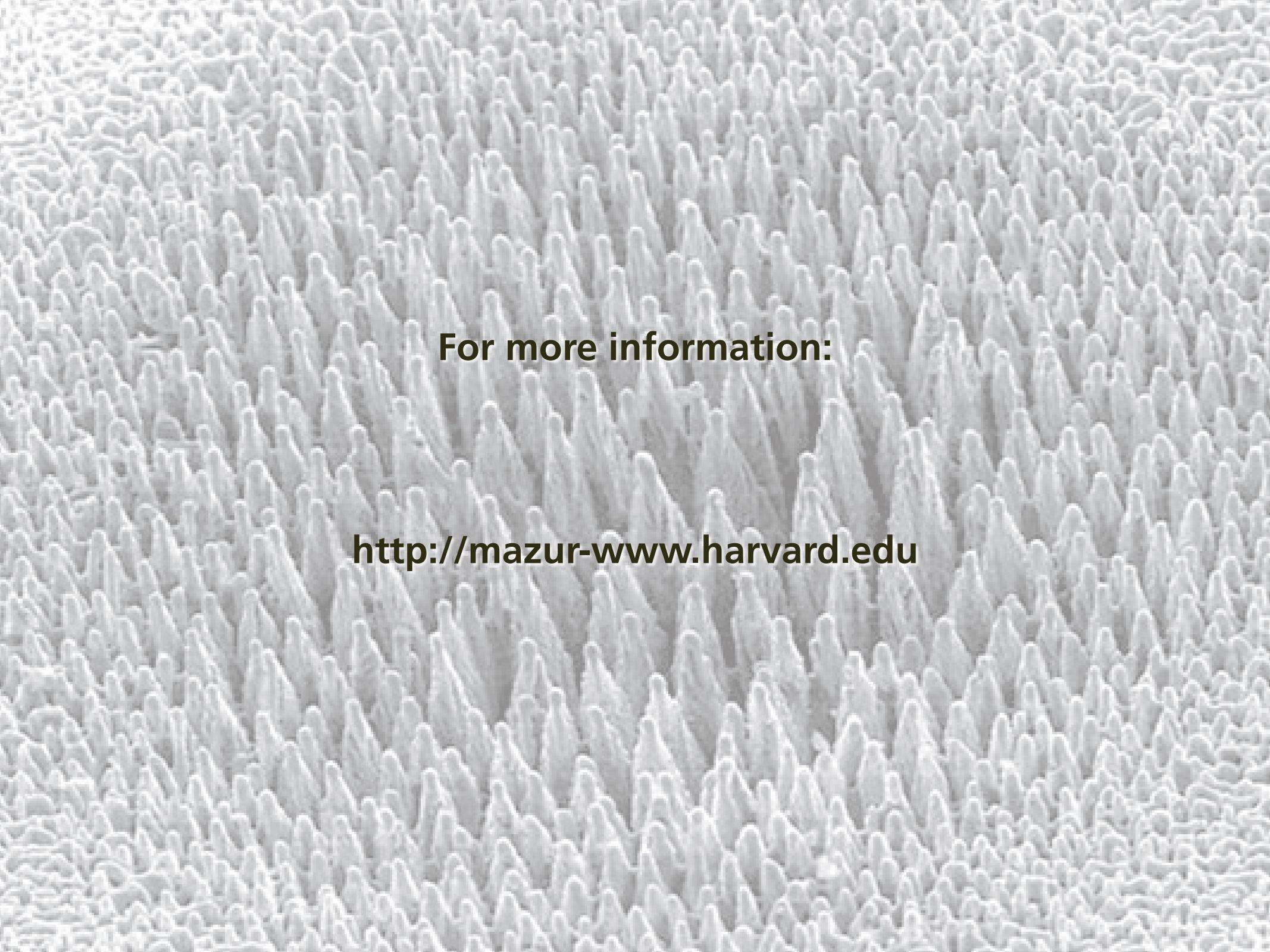
**(CONQUEST beta: [www.conquest.ucl.ac.uk](http://www.conquest.ucl.ac.uk))**

# Needs

- develop tools to model embedding process
- develop tools to model properties of resulting materials
- explore heavily doped materials and their properties

# Conclusion

**High photon flux doping: new class of materials!**

The background of the image is a dense, monochromatic gray. It features a subtle, organic texture composed of numerous small, rounded, and slightly raised elements, giving it a look similar to a field of grass, a microscopic view of a material's surface, or a stylized representation of data visualization. These elements are more concentrated towards the center of the frame.

**For more information:**

**<http://mazur-www.harvard.edu>**